

ABSTRACT

WAFER PROCESSING METHOD

A wafer processing method is provided. The wafer processing method includes a modified layer forming step of applying a laser beam having a transmission wavelength to a wafer along each division line so as to focus the laser beam inside the wafer, thereby forming a modified layer inside the wafer along each division line, a wafer supporting step of attaching an expandable dicing tape to the back side of the wafer and mounting the peripheral portion of the dicing tape to an annular frame before or after performing the modified layer forming step, a tape expanding step of expanding the dicing tape attached to the back side of the wafer, and an air blowing step of blowing air against the wafer in the condition where the dicing tape is expanded, thereby dividing the wafer into individual device chips along each division line where the modified layer is formed and also increasing the spacing between any adjacent ones of the device chips.

[Figure 8A]